

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



FJP13009 High-Voltage Fast-Switching NPN Power Transistor

Features

- · High-Voltage Capability
- · High Switching Speed

Applications

- Electronic Ballast
- Switching Regulator
- Motor Control
- Switched Mode Power Supply

Description

The FJP13009 is a 700 V, 12 A NPN silicon epitaxial planar transistor. The FJP13009 is available with multiple h_{FE} bin classes for ease of design use. The FJP13009 is designed for high speed switching applications which utilizes the industry standard TO-220 package offering flexibility in design and excellent power dissipation.



Ordering Information

Part Number ⁽¹⁾	Top Mark	Package	Packing Method
FJP13009TU	J13009	TO-220 3L	Rail
FJP13009H2TU	J13009-2	TO-220 3L	Rail

Notes

1. The affix "-H2" means the hFE classification. The suffix "-TU" means the tube packing method.

Absolute Maximum Ratings(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	12	Α
I _{CP}	Collector Current (Pulse)	24	Α
I _B	Base Current	6	Α
P _D	Total Device Dissipation (T _C = 25°C)	100	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-65 to +150	°C

Note:

2. These ratings are based on a maximum junction temperature of 150°C. These are steady-state limits. Fairchild Semiconductor should be consulted on application involving pulsed or low-duty-cycle operations.

Electrical Characteristics

Values are at $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 10 \text{ mA}, I_B = 0$	400			V
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 9 \text{ V, } I_{C} = 0$			1	mA
h _{FE1}	DC Current Gain ⁽³⁾	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ A}$	8		40	
h _{FE2}	Do Current Gain	$V_{CE} = 5 \text{ V}, I_{C} = 8 \text{ A}$	6		30	
V _{CE} (sat)	Collector-Emitter Saturation Voltage ⁽³⁾	I _C = 5 A, I _B = 1 A			1.0	1//
		$I_C = 8 \text{ A}, I_B = 1.6 \text{ A}$	= $=$ $=$		1.5	V
		I _C = 12 A, I _B = 3 A			3.0	
V _{BE} (sat)	Base-Emitter Saturation Voltage ⁽³⁾	I _C = 5 A, I _B = 1 A			1.2	V
	Base-Emitter Saturation Voltage	I _C = 8 A, I _B = 1.6 A			1.6	
C _{ob}	Output Capacitance	V _{CB} = 10 V, f = 0.1 MHz		180		pF
f _T	Current Gain Bandwidth Product	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}$	4			MHz
t _{ON}	Turn-On Time	V _{CC} = 125 V, I _C = 8 A,			1.1	
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = 1.6 \text{ A},$			3.0	μs
t _F	Fall Time	$R_L = 15.6 \Omega$			0.7	

Note:

3. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2%

h_{FE} Classification

Classification	H1	H2
h _{FE1}	8 ~ 17	15 ~ 28

2

Typical Performance Characteristics

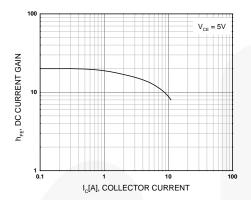


Figure 1. DC Current Gain

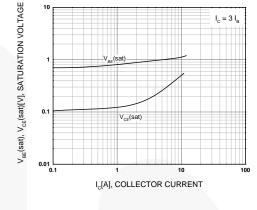


Figure 2. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

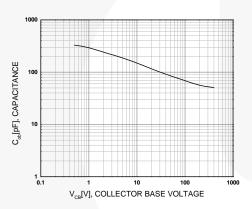


Figure 3. Collector Output Capacitance

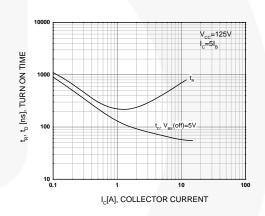


Figure 4. Turn-On Time

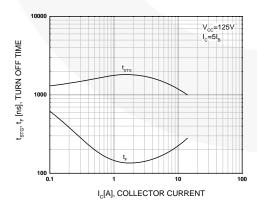


Figure 5. Turn-Off Time

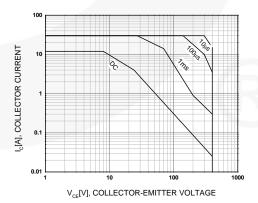


Figure 6. Forward Bias Safe Operating Area

Typical Performance Characteristics (Continued)

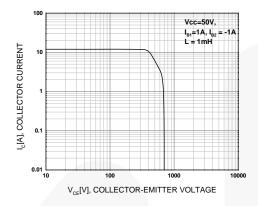


Figure 7. Reverse Bias Safe Operating Area

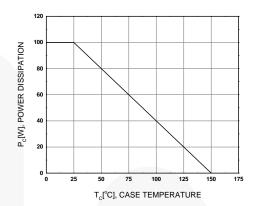


Figure 8. Power Derating



ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative